

Features

- 100V/12A,
 $R_{DS(ON)} = 95m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 105m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

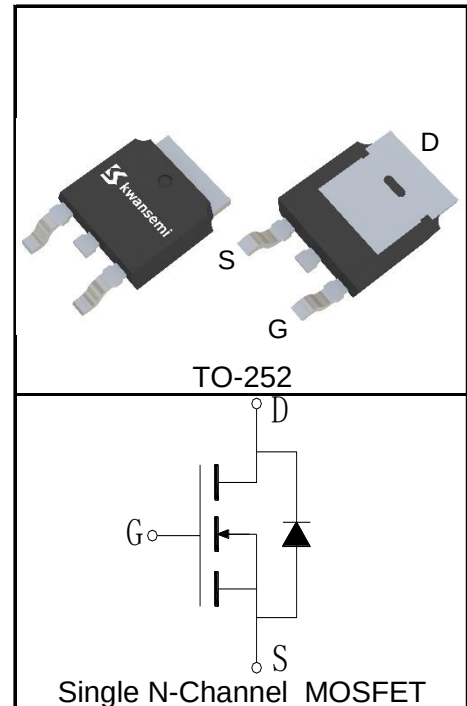
Applications

- Power Switching Appliaction
- Load Switching



Halogen-Free

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	
T _{Jmax}	Maximum Junction Temperature		175	°C
T _J ,T _{STG}	Operating and Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	12	A
Mounted on Large Heat Sink				
I _{DP} ^①	Pulse Drain Current	T _C =25°C	48	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	12	A
		T _C =100°C	8	
P _D	Maximum Power Dissipation	T _C =25°C	41	W
		T _C =100°C	20	
R _{θJC}	Thermal Resistance-Junction to Case		3.6	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		100	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		25	mJ

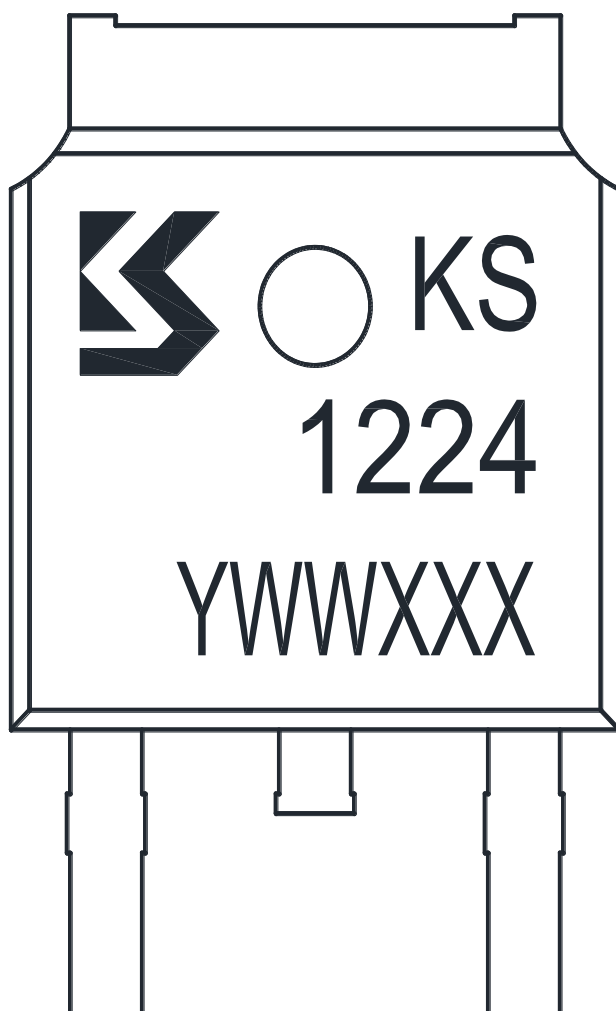
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS1224DA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.1	1.5	2.3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =10A		95	120	mΩ
		V _{GS} =4.5V, I _{DS} =8A		105	130	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =10A, V _{GS} =0V		0.89	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =10A, dI _{SD} /dt=100A/μs		14		ns
Q _{rr}	Reverse Recovery Charge			24		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		2.1		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, Frequency=1.0MHz		810		pF
C _{oss}	Output Capacitance			25		
C _{rss}	Reverse Transfer Capacitance			20		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =50V, I _{DS} =10A, V _{GEN} =10V, R _G =3Ω		8		ns
t _r	Turn-on Rise Time			10		
t _{d(OFF)}	Turn-off Delay Time			16		
t _f	Turn-off Fall Time			8		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _{DS} =10A		20		nC
Q _{gs}	Gate-Source Charge			2		
Q _{gd}	Gate-Drain Charge			4.6		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = 11A$, $L = 0.5\text{mH}$, $V_{DD} = 48V$, $R_G = 25\Omega$, $V_{GS} = 10V$. Part not recommended for use above this value. 100% Final Test at $I_{AS} = 8A$, $L = 0.5\text{mH}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS1224DA	TO-252	Tape&Reel	2500	13"	16mm

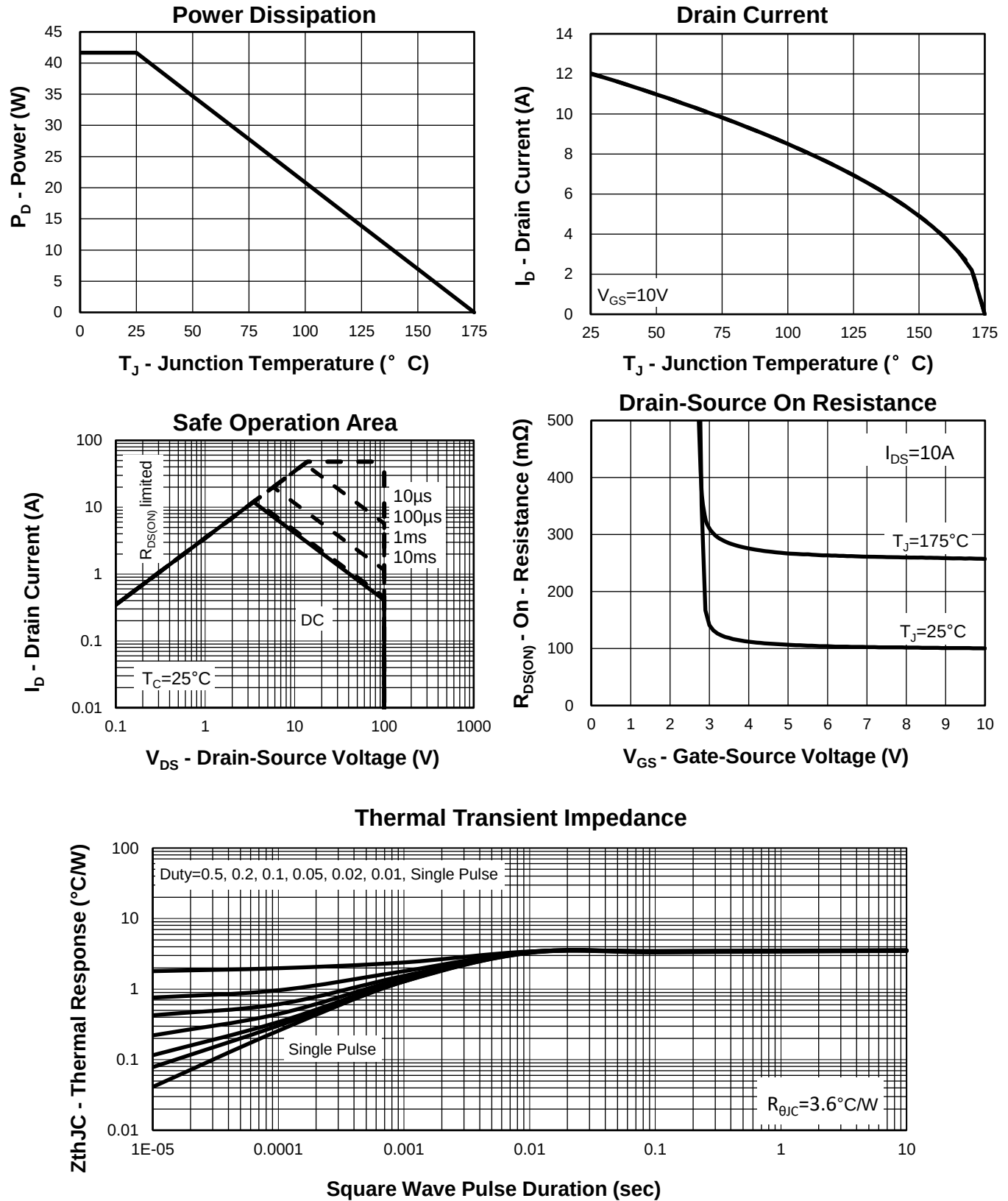


1st Line: Kwansemi LOGO, Kwansemi Code(KS)

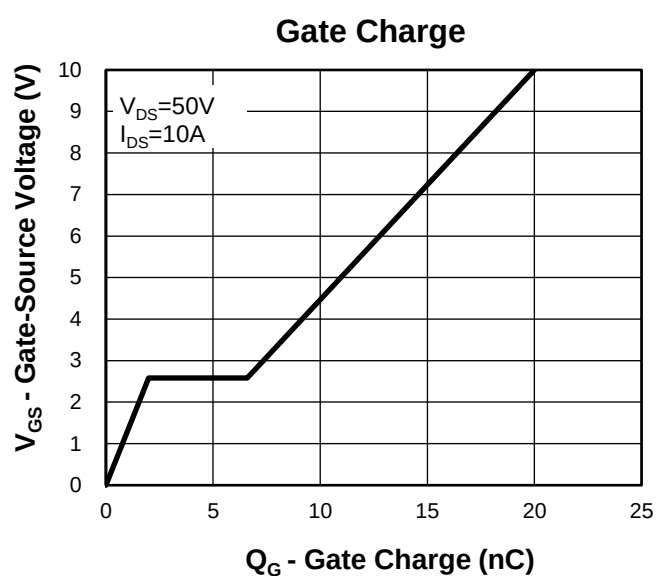
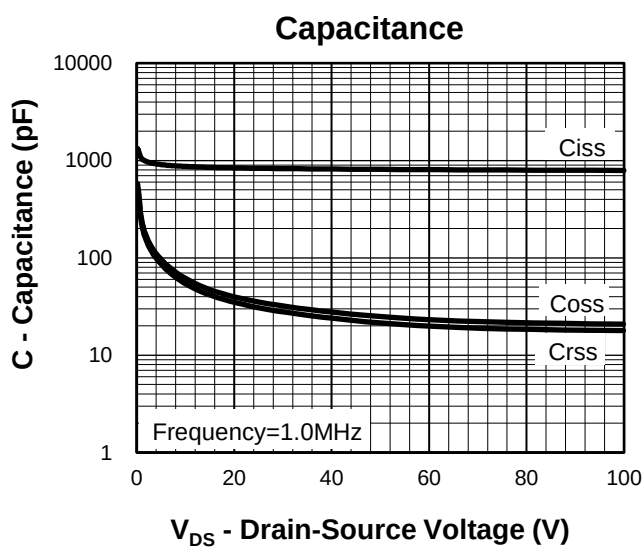
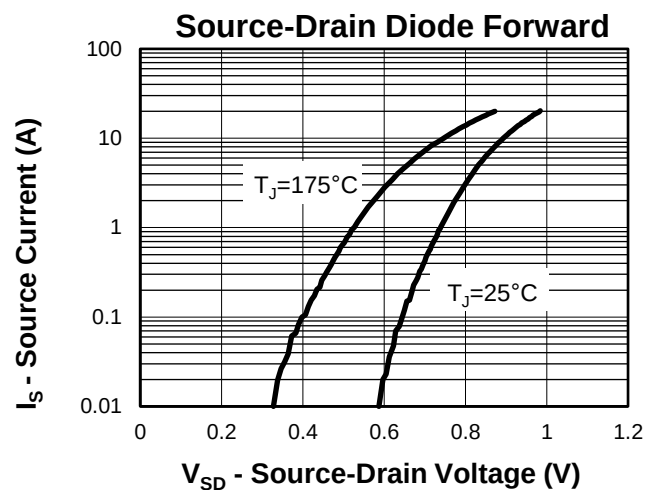
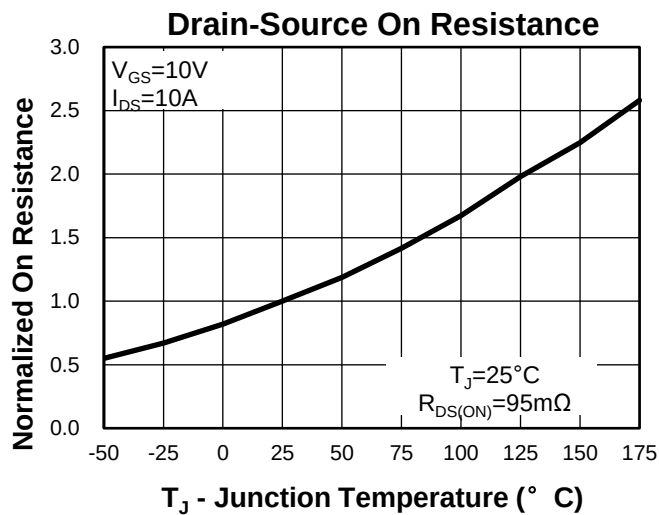
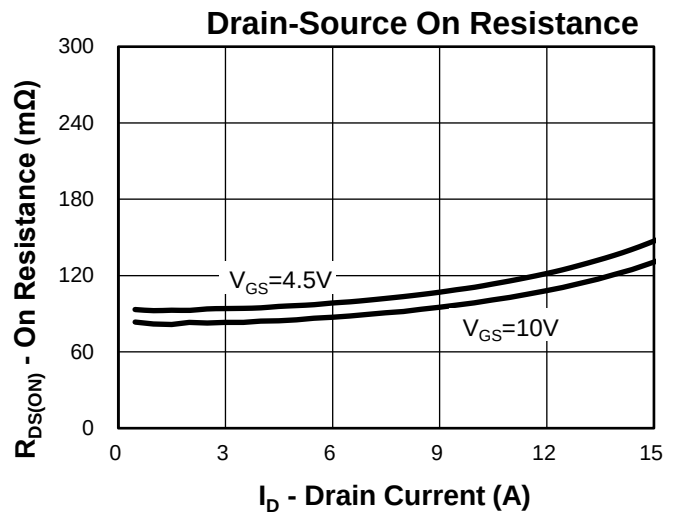
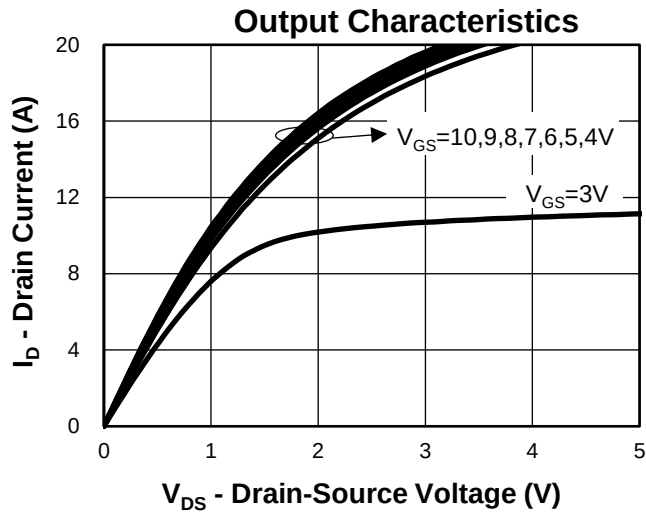
2nd Line: Part Number(1224)

3rd Line: Lot Number(YWWXXX)

Typical Characteristics

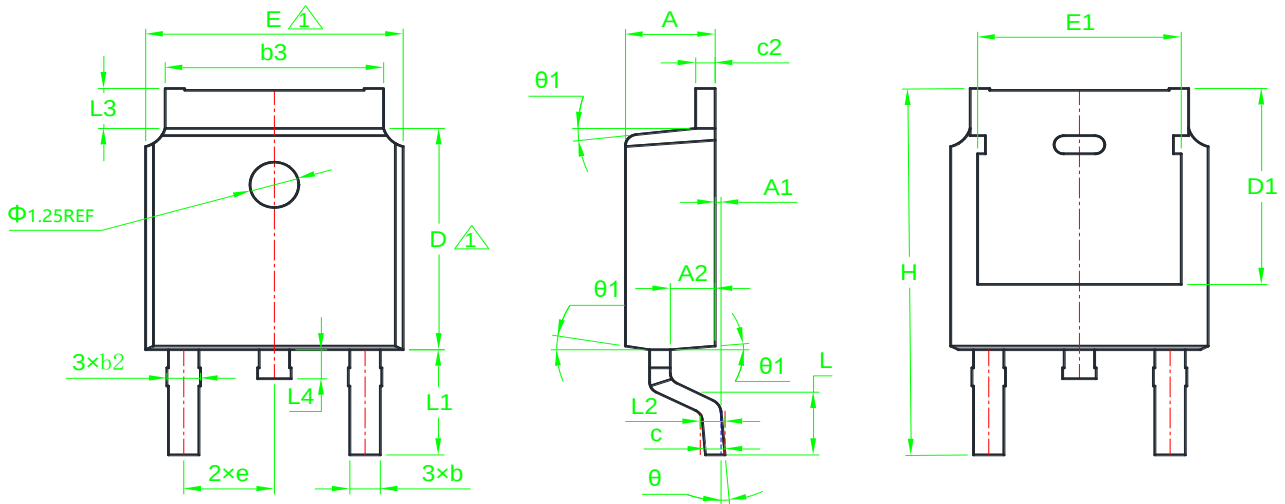


Typical Characteristics



Package Information

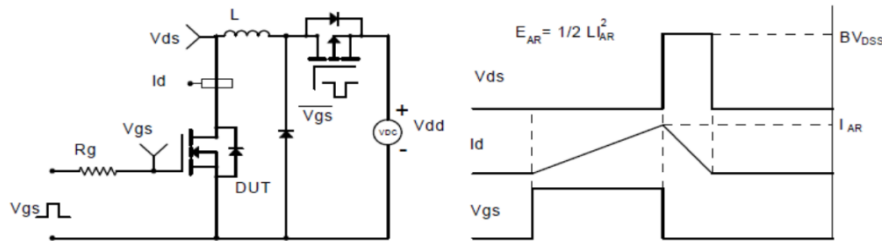
TO-252



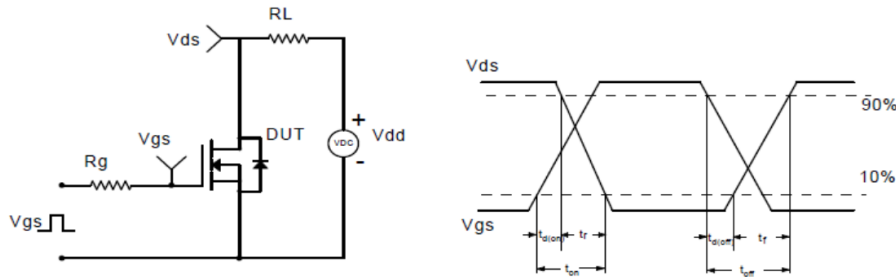
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	2.20	2.30	2.38	0.087	0.091	0.094	E	6.40	6.60	6.70	0.252	0.260	0.264
A1	0.00	*	0.15	0.000	*	0.006	E1	4.55	*	5.15	0.179	*	0.203
A2	0.90	1.00	1.10	0.035	0.039	0.043	H	9.60	10.10	10.40	0.378	0.398	0.409
b	0.65	0.75	0.85	0.026	0.030	0.033	L	1.40	1.50	1.70	0.055	0.059	0.067
b2	0.72	*	0.90	0.028	*	0.035	L1	2.90REF			0.114REF		
b3	5.13	5.33	5.46	0.202	0.210	0.215	L2	0.508BSC			0.020BSC		
c	0.47	0.51	0.54	0.019	0.020	0.021	L3	0.90	*	1.25	0.035	*	0.049
D	6.00	6.10	6.20	0.236	0.240	0.244	L4	0.60	*	1.00	0.024	*	0.039
D1	5.25	5.35	5.60	0.207	0.211	0.220	θ	0°	*	10°	0°	*	10°
e	2.286BSC			0.090BSC			θ1	5°	*	9°	5°	*	9°

 Dimensions D and E do not include mold flash protrusions or gate burrs.

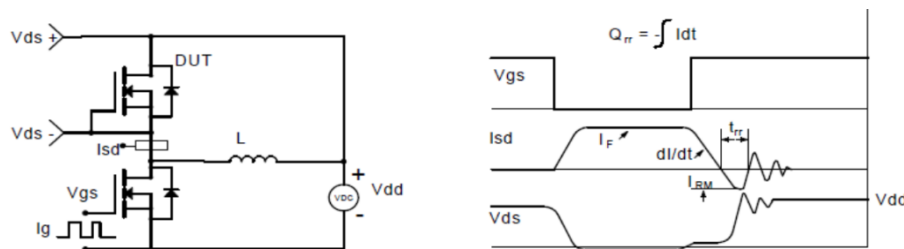
Avalanche Test Circuit and Waveforms



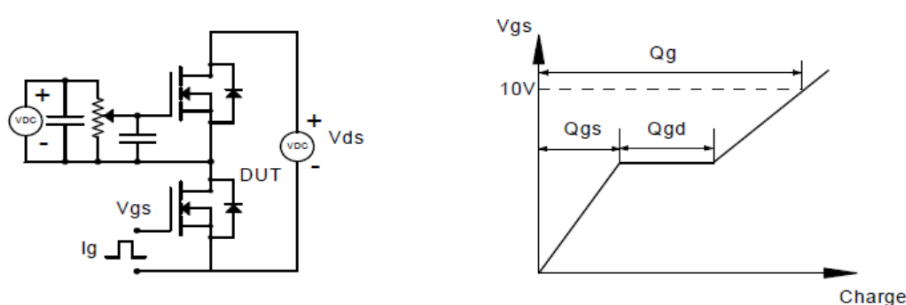
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

Kwansemi Semiconductor Co.,Ltd

Email:Sales@kwansemi.com

Web:www.kwansemi.com

DISCLAIMER:

Kwansemi reserves the right to change the specifications and circuitry without notice at any time. The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.